

# US-Lasers: 904nm-30mW - Infrared Laser Diode

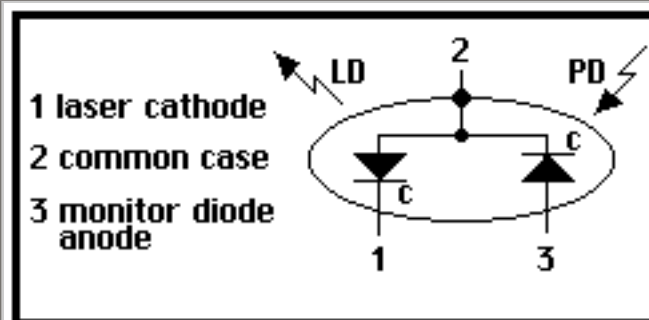
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## IR LASER DIODE DATA SHEET

ABSOLUTE MAXIMUM RATINGS - ( $T_c=25\text{ }^\circ\text{C}$ )

### TECHNICAL DATA

IR light output	904nm
Optical power output	30mW CW
Package Type	5.6mm
Built-in photo diode for monitoring laser output	



Pin Out Diagram

Items	Symbols	Values	Unit
Optical output power	Po	30	mW
Laser diode reverse voltage	V	2	V
Photo diode reverse voltage	V	30	V
Operating temperature	Topr	-10 ~ +50	°C
Storage temperature	Tstg	-40 ~ +85	°C

### OPTICAL and ELECTRICAL CHARACTERISTICS - ( $T_c=25\text{ }^\circ\text{C}$ )

Items	Symbols	Min.	Typ.	Max.	Unit	Test Condition
Optical output power	Po	-	30	-	mW	-
Threshold current	Ith	30	40	50	mA	Po=30mW
Operating current	Iop	60	80	100	mA	Po=30mW
Operating voltage	Vop	2.0	2.2	2.7	V	Po=30mW
Lasing wavelength	ep	885	904	920	nm	Po=30mW
Beam divergence		8	10	11	deg	Po=30mW
Beam divergence		25	31	40	deg	Po=30mW
Monitor current	Im	100	300	500	uA	Po=30mW
Astigmatism	As	-	11	-	um	Po=30mW
Slope Efficiency (mW/mA)		0.5	0.7	0.9		Po=30mW
MTTF			10000 hrs.			Po=30mW
Emitter Size	10 x 60 Microns - Emitter Distance to Cap Lens = 0.3mm					
Structure	Index Guided					

- 15mm Module Housing Available: 14.8mm x 33.5mm - 3/8 - 56 Thread Size